

PBSS4360ZX Datasheet

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DiGi Electronics Part Number PBSS4360ZX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS4360ZX

Description TRANS NPN 60V 3A SOT223

Detailed Description Bipolar (BJT) Transistor NPN 60 V 3 A 145MHz 650 m

W Surface Mount SOT-223



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PBSS4360ZX	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	3 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	400mV @ 300mA, 3A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	200 @ 50mA, 5V
Power - Max:	Frequency - Transition:
650 mW	145MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223
Base Product Number:	
PBSS4360	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):	
ROHS3 Compliant	1 (Unlimited)	
REACH Status:	ECCN:	
REACH Unaffected	EAR99	
HTSUS:		
8541.21.0075		



PBSS4360Z

60 V, 3 A NPN low VCEsat (BISS) transistor

26 February 2014

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5360Z.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	$t_p \le 1$ ms; single pulse	-	-	6	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$; T_{amb} = 25 °C	-	-	140	mΩ



60 V, 3 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	E	emitter		. 1
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym016

6. Ordering information

Table 3. Ordering information

Type number	ber Package		
	Name	Description	Version
PBSS4360Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

9	
Type number	Marking code
PBSS4360Z	P4360Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	6	Α
I _B	base current			-	500	mA
I _{BM}	peak base current	t _p ≤ 1 ms; single pulse		-	1	Α
P _{tot}	total power dissipation		[1]	-	0.65	W
			<u>[2]</u>	-	1	W
			[3]	-	1.35	W

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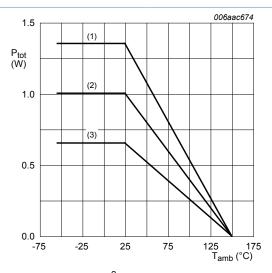
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Symbol	Parameter	Conditions		Min	Max	Unit
			<u>[4]</u>	-	2	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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60 V, 3 A NPN low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	192	K/W
		<u>[2]</u>	-	-	125	K/W	
	ambient		[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

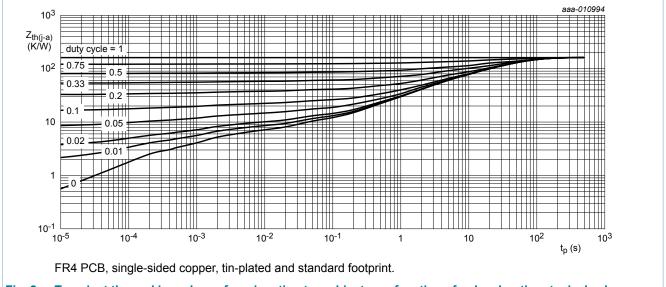
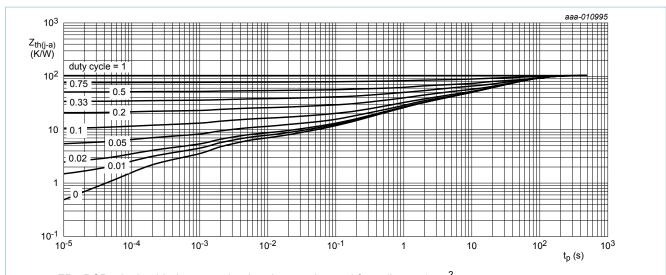


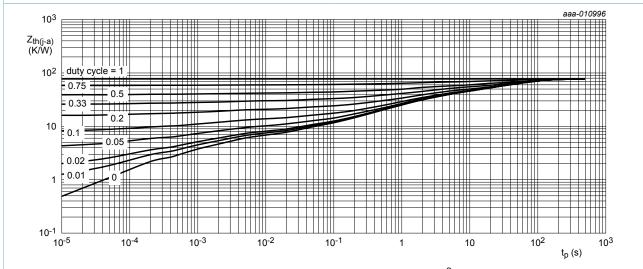
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

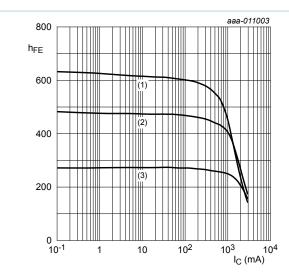
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = 48 V; I_{E} = 0 A; T_{amb} = 25 °C	-	-	100	nA
current		V_{CB} = 48 V; I_{E} = 0 A; T_{j} = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
l _{ЕВО}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 50 mA; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 5 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	120	-	-	
		V_{CE} = 5 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	75	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 500 mA; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	75	mV
		I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	150	mV
		I_{C} = 2 A; I_{B} = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	275	mV
		I_{C} = 3 A; I_{B} = 300 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	400	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 2 A; I_{B} = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	140	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.1	V
fτ	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	75	145	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	11	14	pF

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$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values

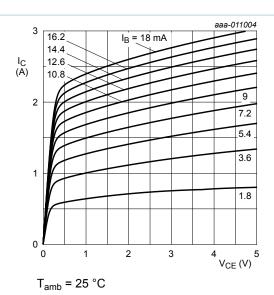
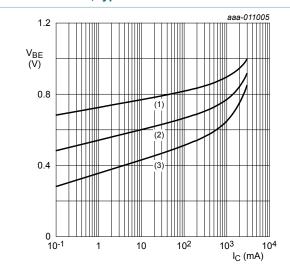


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



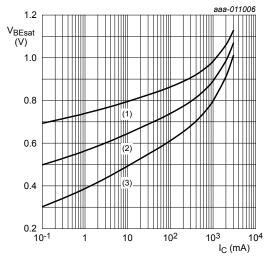
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

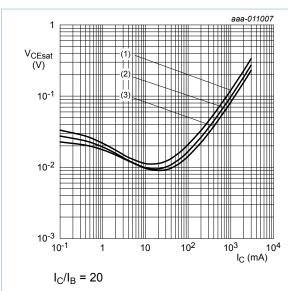
(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

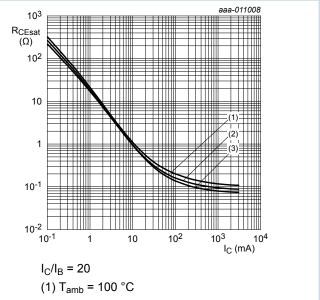
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- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) T_{amb} = 25 °C
- $(3) T_{amb} = -55 °C$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



- (2) T_{amb} = 25 °C
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

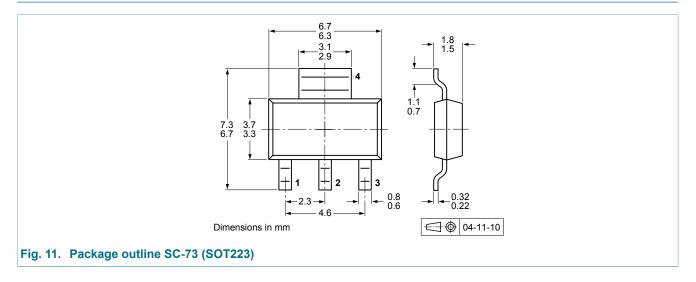
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11. Test information

11.1 Quality information

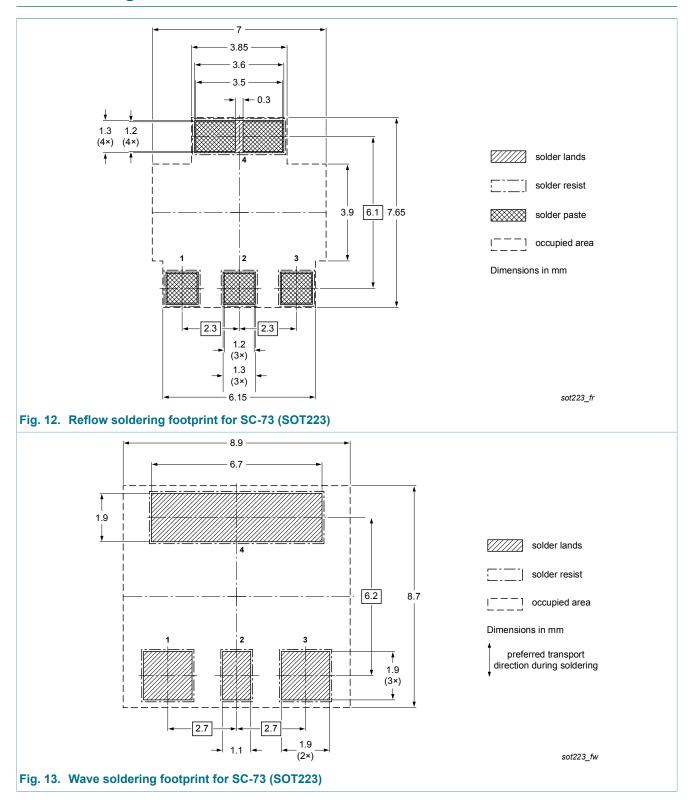
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



60 V, 3 A NPN low VCEsat (BISS) transistor

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4360Z v.1	20140226	Product data sheet	-	-

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15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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